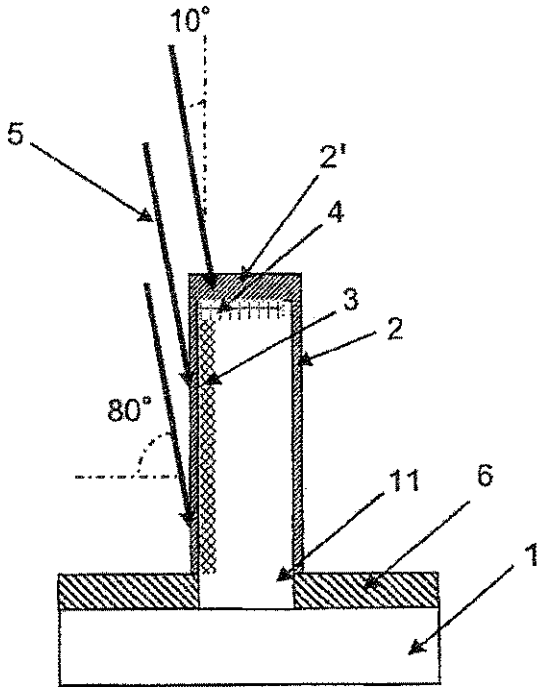


FIG. 1A

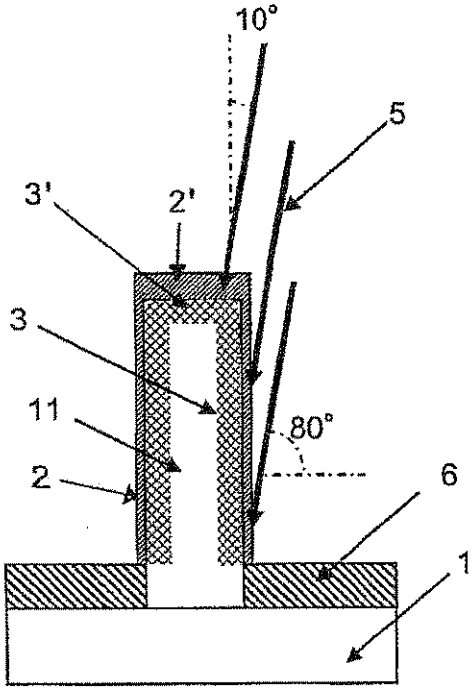


FIG. 1B

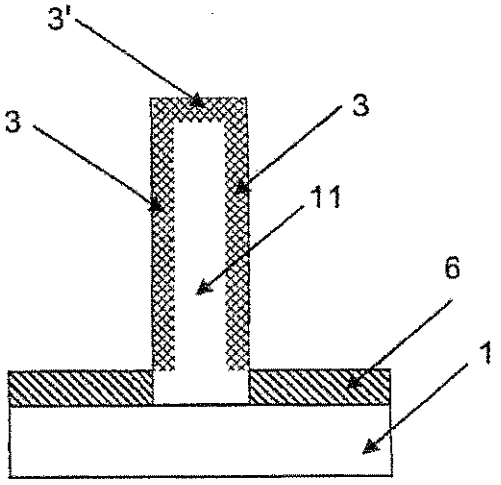


FIG. 1C

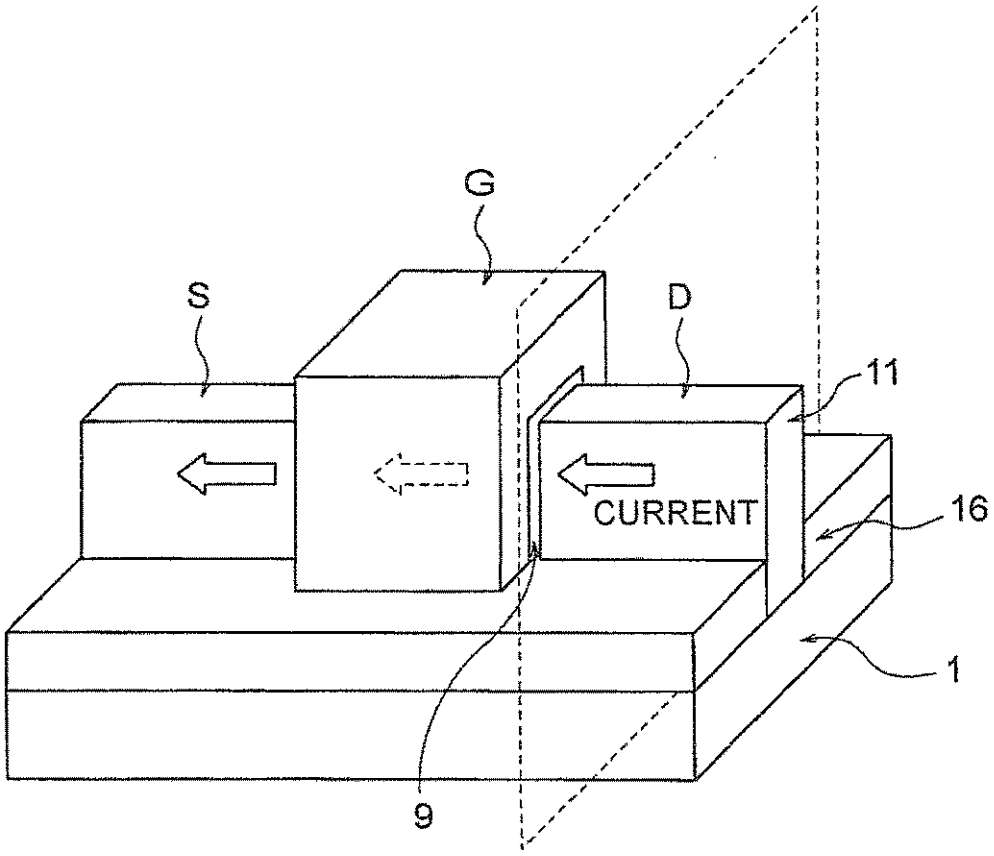


FIG. 2

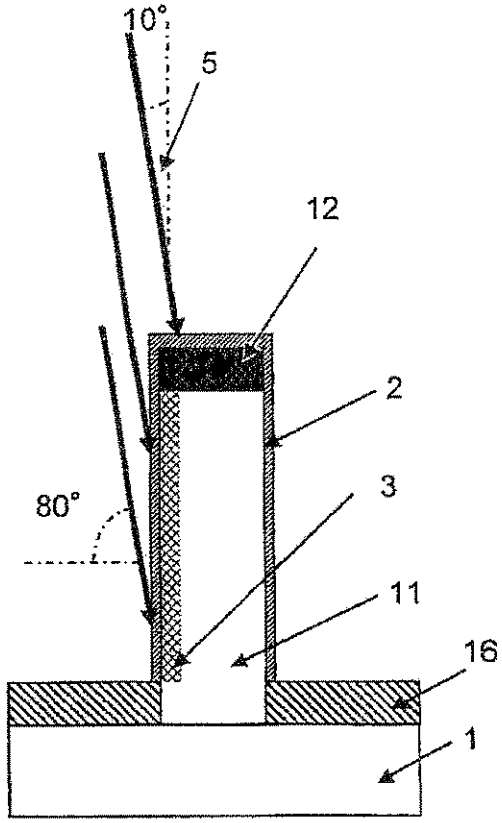


FIG. 3A

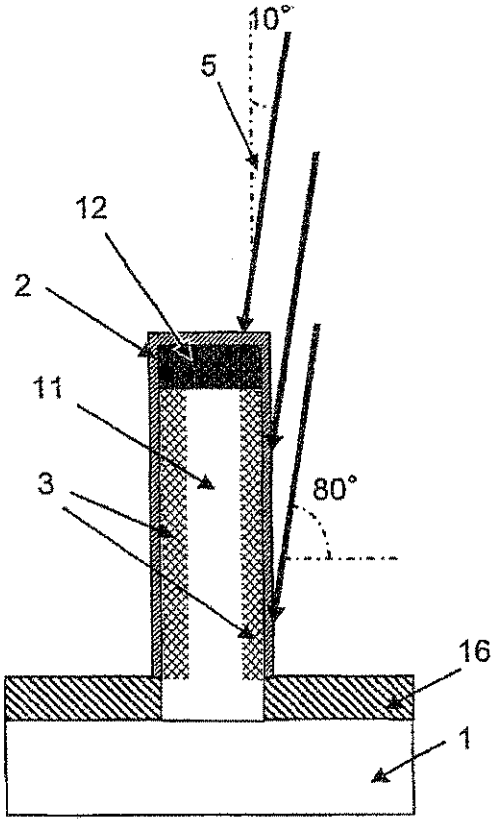


FIG. 3B

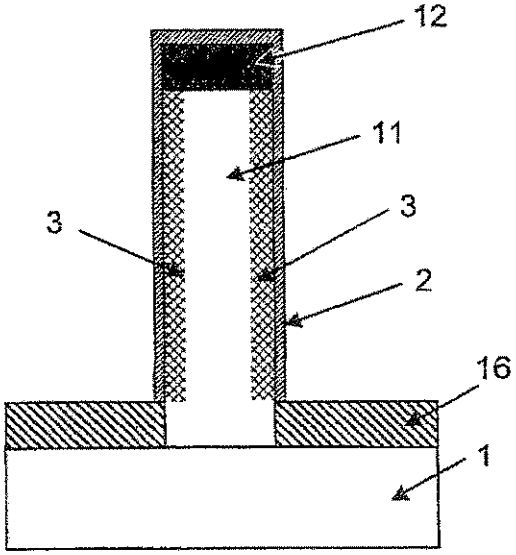


FIG. 3C

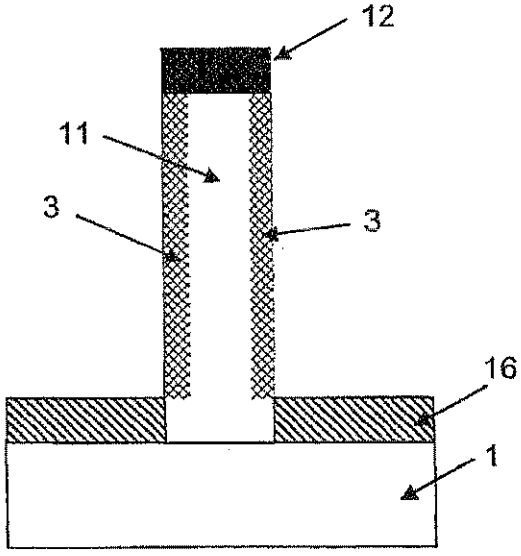


FIG. 3D

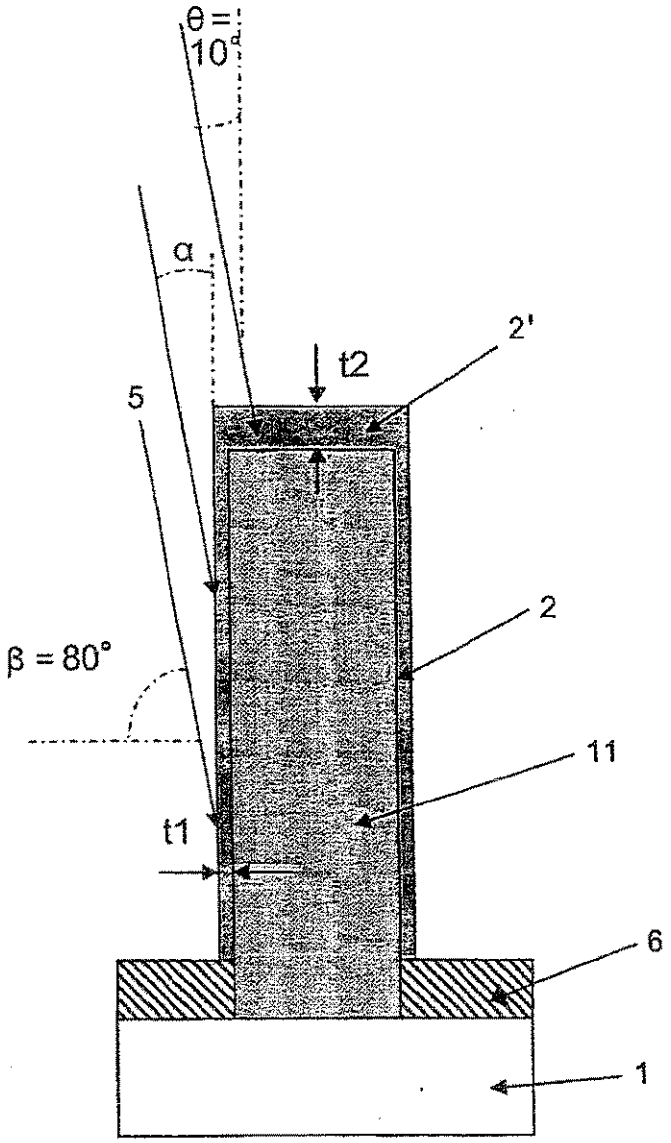


FIG. 4

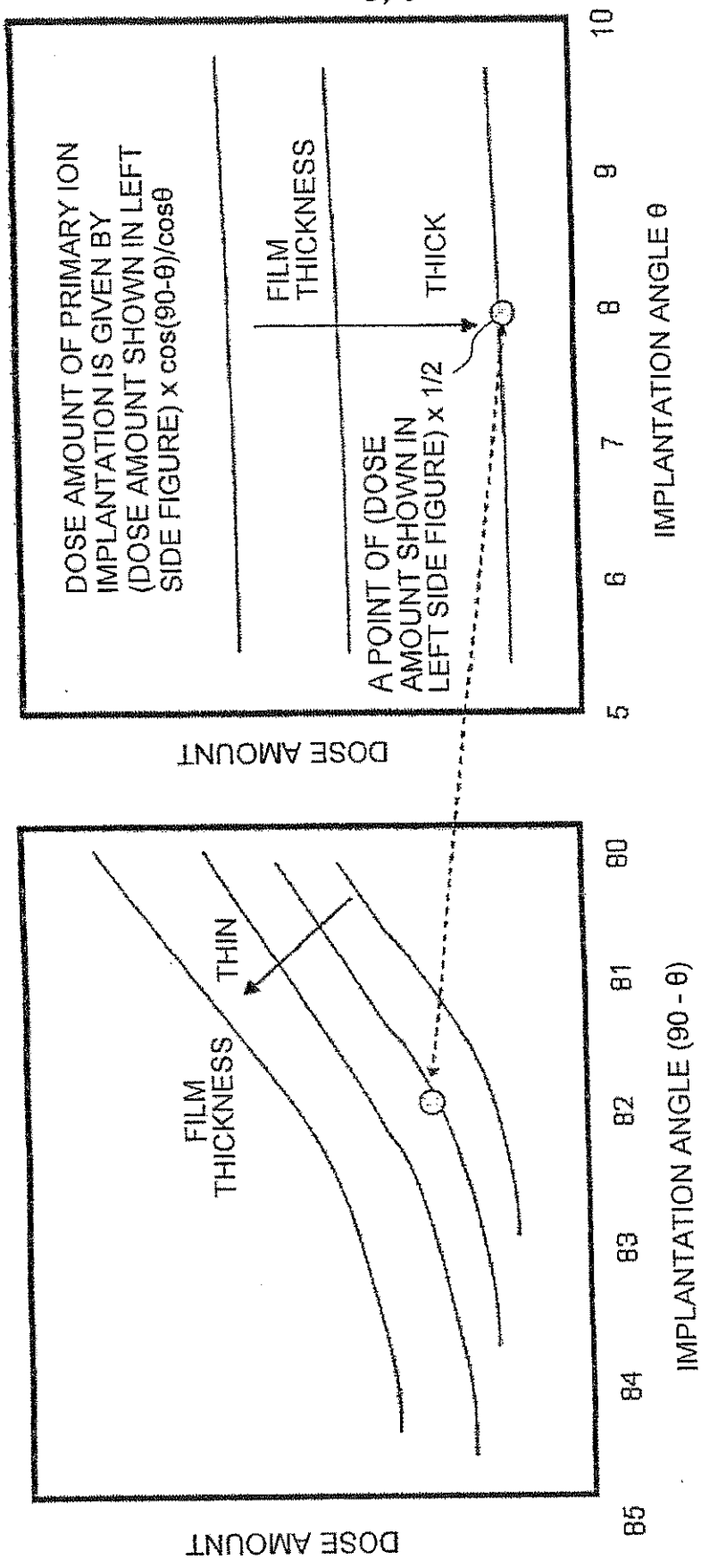

DOSE AMOUNT OF PRIMARY ION IMPLANTATION IS GIVEN BY (DOSE AMOUNT SHOWN IN LEFT SIDE FIGURE) x cos(90-θ)/cosθ
FILM THICKNESS
A POINT OF (DOSE AMOUNT SHOWN IN LEFT SIDE FIGURE) x 1/2
THICK
DOSE AMOUNT
5
6
7
8
9
10
IMPLANTATION ANGLE θ
FILM THICKNESS
THIN
DOSE AMOUNT
85
84
83
82
81
80
IMPLANTATION ANGLE (90 - θ)

FIG. 5

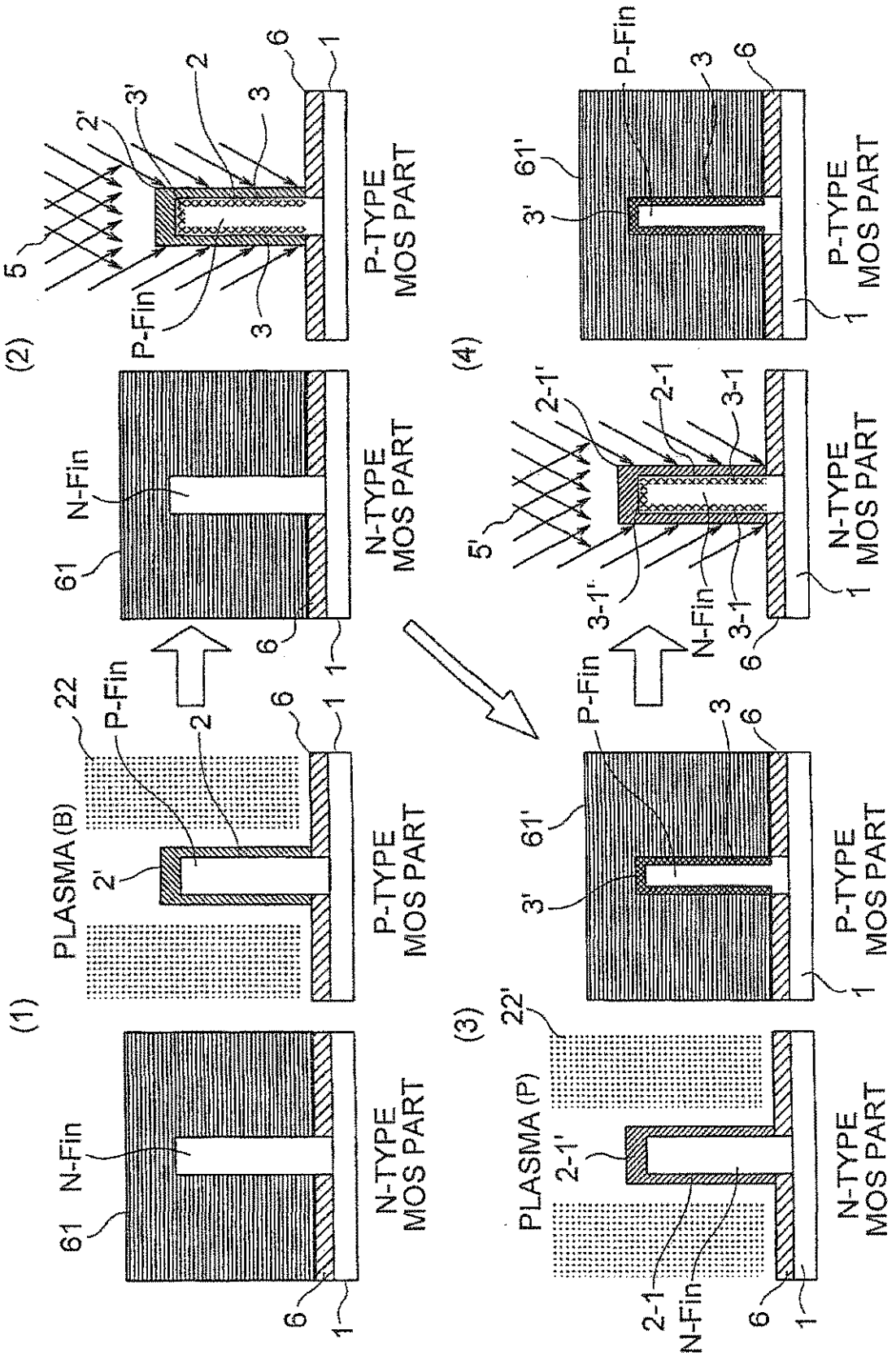

(1)
61 N-Fin
6
1
N-TYPE MOS PART
PLASMA (B)
22
P-Fin
2'
2
6
1
P-TYPE MOS PART
(2)
5
2'
3'
2
3
6
1
P-Fin
3
N-Fin
61
6
1
N-TYPE MOS PART
(3)
22'
PLASMA (P)
2-1'
2-1
N-Fin
6
1
N-TYPE MOS PART
P-Fin
3
6
3'
61'
1
P-TYPE MOS PART
(4)
5'
2-1'
2-1
3-1
3-1'
N-Fin
3-1
6
1
N-TYPE MOS PART
P-Fin
3
6
3'
61'
1
P-TYPE MOS PART

FIG. 6

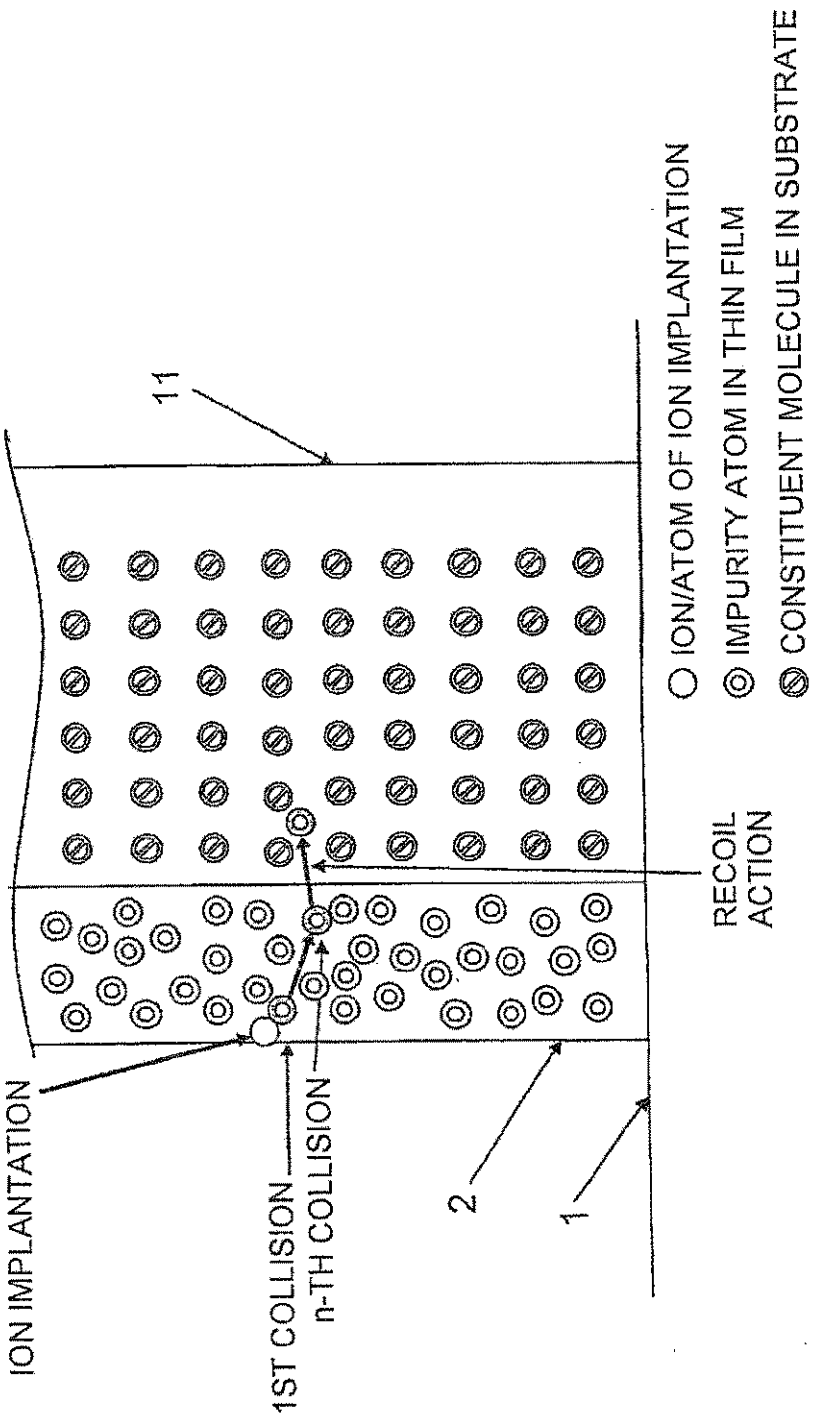

11
ION IMPLANTATION
1ST COLLISION
n-TH COLLISION
2
1
RECOIL ACTION
ION/ATOM OF ION IMPLANTATION
IMPURITY ATOM IN THIN FILM
CONSTITUENT MOLECULE IN SUBSTRATE

FIG. 7

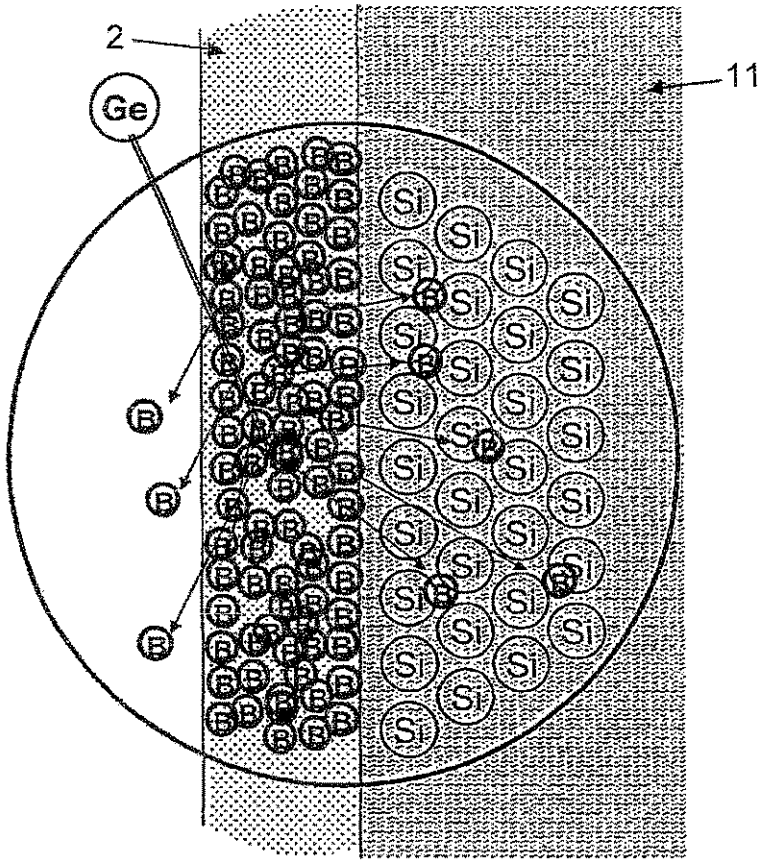


FIG. 8